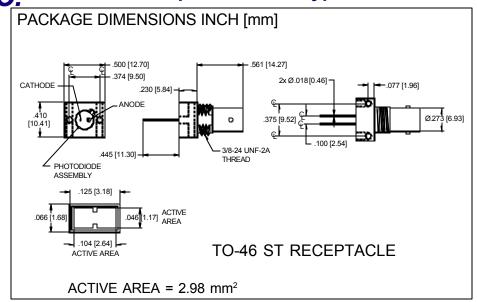
PHOTONIC Silicon Photodiode, Blue Enhanced Photoconductive **DETECTORS INC.** Hermetic Fiber Optic Detector Type PDB-C504-ST





FEATURES

- High speed
- Low capacitance
- Blue enhanced
- Low dark current

DESCRIPTION

The PDB-C504-ST is a silicon, PIN planar diffused, blue enhanced photodiode. Ideal for high speed photoconductive applications. Packaged in a hermetic, TO-46 ST receptacle.

APPLICATIONS

- Industrial controls
- Video systems
- Laser power monitors
- Fiber optic links

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS	
$V_{\mathtt{BR}}$	Reverse Voltage		100	V	
T_{STG}	Storage Temperature	-55	+150	⊙C	
T _O	Operating Temperature Range	-40	+125	⊙C	
T _s	Soldering Temperature*		+240	∘C	
١ _L	Light Current		500	mA	

^{*1/16} inch from case for 3 secs max

SPECTRALRESPONSE RESPONSIVITY (A/W) 0.6 0.5 0.4 0.3

0.2

WAVELENGTH(nm)

190 300 400 500 600 700 800 900 000 200

ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

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SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS			
l _{sc}	Short Circuit Current	H = 100 fc, 2850 K	40	45		μ A			
I _D	Dark Current	H = 0, V _R = 10 V		.15	1.0	nA			
R _{SH}	Shunt Resistance	$H = 0, V_R = 10 \text{ mV}$	0.5	1.0		GΩ			
TCR _{SH}	RSH Temp. Coefficient	$H = 0, V_R = 10 \text{ mV}$		-8		% / °C			
C _J	Junction Capacitance	H = 0, V _R = 10 V**		10		pF			
λrange	Spectral Application Range	Spot Scan	350		1100	nm			
λр	Spectral Response - Peak	Spot Scan		950		nm			
V _{BR}	Breakdown Voltage	I = 10 μA	70	100		V			
NEP	Noise Equivalent Power	V _R = 10 V @ Peak		1.5x10 ⁻¹⁴		W/ √Hz			
tr	Response Time	RL = 1 K Ω V _R = 50 V		10		nS			